华润微电子(重庆)有限公司

CRJZ99N65G2

SJMOS N-MOSFET 650V, 85mΩ, 28A

Features

- CRM(CQ) Super_Junction technology
- Much lower Ron*A performance for On-state efficiency
- Better efficiency due to very low FOM
- Qualified for industrial grade applications according to JEDEC

Product Summary

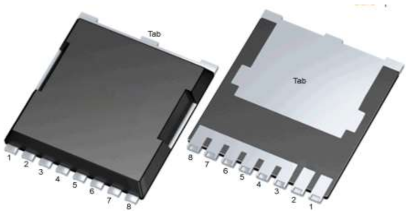
VDS	650V
$R_{DS(on)\_typ}$	85mΩ
I_D	28A

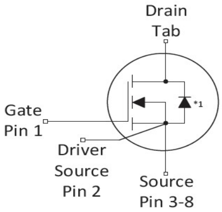
Applications

- LED/LCD/PDP TV and monitor Lighting
- Solar/Renewable/UPS-Micro Inverter System
- Charger
- Power Supply

100% DVDS Tested

100% Avalanche Tested





1: Internal body diode

Package Marking and Ordering Information

Part #	Marking	Package	Packing	Reel Size	Tape Width	Qty
CRJZ99N65G2	JZ99N65G2	TOLL	Tape&Reel	N/A	N/A	2000pcs

Absolute Maximum Ratings

Parameter	**Symbol**	**Value**	**Unit**
Drain-source voltage	V_{DS}	650	V
Continuous drain current [1] T_C = 25°C T_C = 100°C	I_D	 28 18	A
Pulsed drain current [2](T_C = 25°C, t_p limited by T_{jmax})	$I_{D\ pulse}$	112	A
Avalanche energy, single pulse (L=30mH)	E_{AS}	480	mJ
MOSFET dv/dt ruggedness	dv/dt	50	V/ns
Gate-Source voltage	V_{GS}	±30	V
Power dissipation (T_C = 25°C)	P_{tot}	198	W
Continuous diode forward current(T_C = 25°C)	I_S	28	A
Diode pulse current [2] (T_C = 25°C)	$I_{S\ pulse}$	112	A
Recovery diode dv/dt [3]	dv/dt	50	V/ns
Operating junction and storage temperature	T_j , T_{stg}	-55...+150	°C

1) Limited by Tj,max. Maximum Duty Cycle D = 0.50
2) Pulse width tp limited by Tj,max
3) Identical low side and high side switch with identical RG

Thermal Resistance

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Thermal resistance, junction – case	R_{thJC}	-	0.45	0.63	°C/W	
Thermal resistance, junction – ambient	R_{thJA}	-	-	56	°C/W	

Electrical Characteristic (at Tj = 25 °C, unless otherwise specified)

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Static Characteristic						
Drain-source breakdown voltage	BV_{DSS}	650	-	-	V	V_{GS}=0V, I_D=250uA
Gate threshold voltage	$V_{GS(th)}$	3	-	4	V	V_{DS}=V_{GS},I_D=250uA
Zero gate voltage drain current	I_{DSS}	- -	- 10	1 -	μA	V_{DS}=650V,V_{GS}=0V T_j=25°C T_j=150°C
Gate-source leakage current	I_{GSS}	-	-	±100	nA	V_{GS}=±30V,V_{DS}=0V
Drain-source on-state resistance	$R_{DS(on)}$	- -	85 205	99 -	mΩ	V_{GS}=10V, I_D=17A, T_j=25°C T_j=150°C
Transconductance	g_{fs}	-	30	-	S	V_{DS}=20V,I_D=17A
Dynamic Characteristic						
Input Capacitance	C_{iss}	-	2400	-	pF	V_{GS}=0V, V_{DS}=100V, f=1MHz
Output Capacitance	C_{oss}	-	110	-		
Reverse Transfer Capacitance	C_{rss}	-	1.6	-		
Gate Total Charge	Q_G	-	70	-	nC	V_{GS}=10V, V_{DS}=480V, I_D=17A
Gate-Source charge	Q_{gs}	-	16	-		
Gate-Drain charge	Q_{gd}	-	28	-		
Gate plateau voltage	$V_{plateau}$	-	5.7	-	V	
Turn-on delay time	$t_{d(on)}$	-	37	-	ns	V_{GS}=10V, I_D=17A, V_{DS}=400V, R_g=27Ω
Rise time	t_r	-	43	-		
Turn-off delay time	$t_{d(off)}$	-	254	-		
Fall time	t_f	-	40	-		
Gate resistance	R_{gint}	-	0.9	-	Ω	f=1MHz

Body Diode Characteristic

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Body Diode Forward Voltage	V_{SD}	0.6	0.86	1.1	V	V_{GS}=0V,I_{SD}=17A
Body Diode Reverse Recovery Time	t_{rr}	-	347		ns	Isd=17A dI/dt=100A/us Vds=400V
Body Diode Reverse Recovery Charge	Q_{rr}	-	6		uC	

Typical Performance Characteristics

Fig 1. Output Characteristics (Tj=25℃)

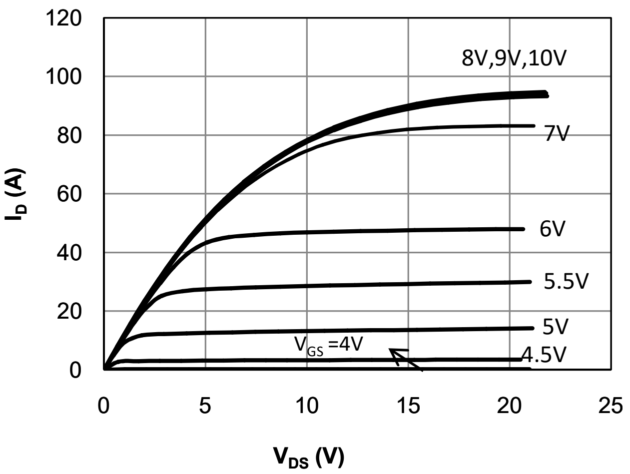


Fig 2. Output Characteristics (Tj=150℃)

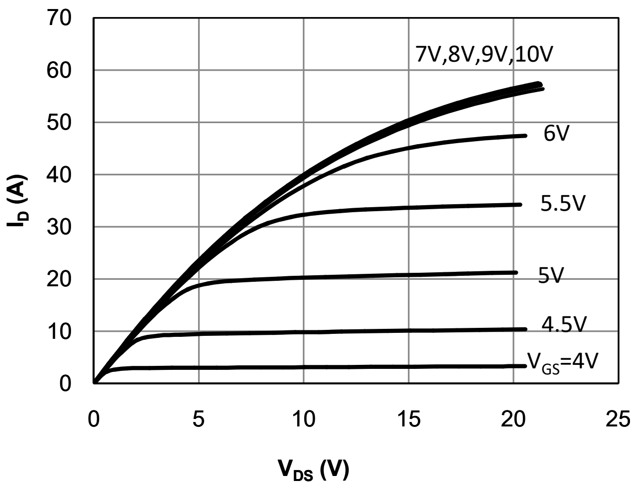


Fig 3: Transfer Characteristics

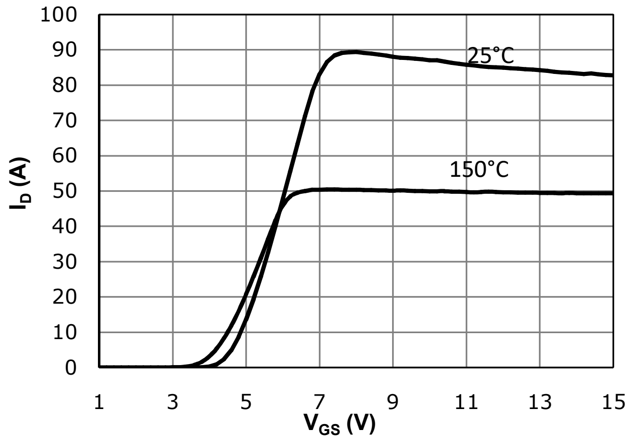


Fig 4: V_{TH} Vs Tj Temperature Characteristics

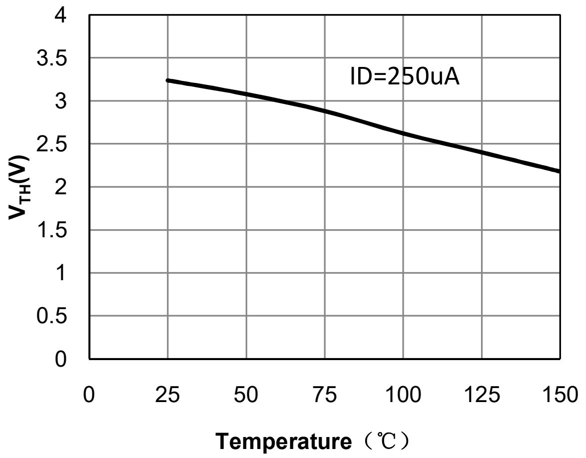


Fig 5: Rdson Vs Ids Characteristics(Tj=25℃)

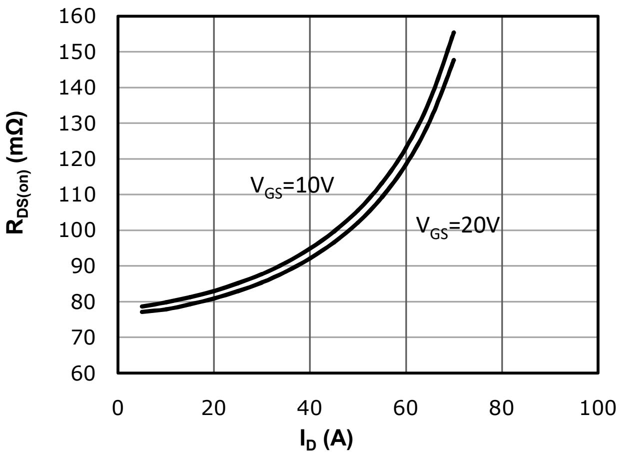


Fig 6: Rds(on) vs. Temperature

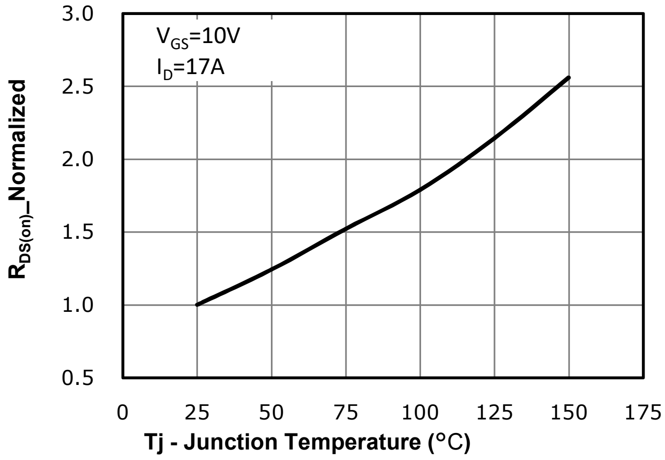


Fig 7: BVDSS vs. Temperature

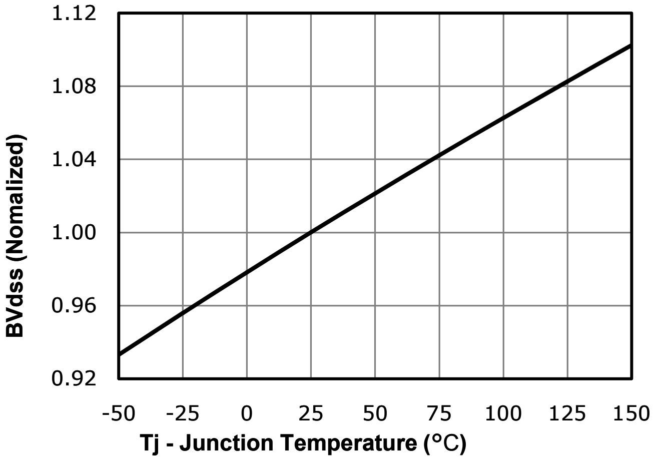


Fig 8: Rds(on) vs Gate Voltage

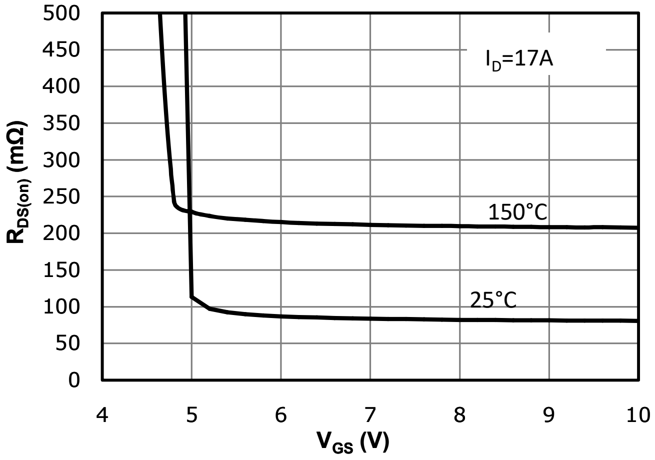


Fig 9: Body-diode Forward Characteristics

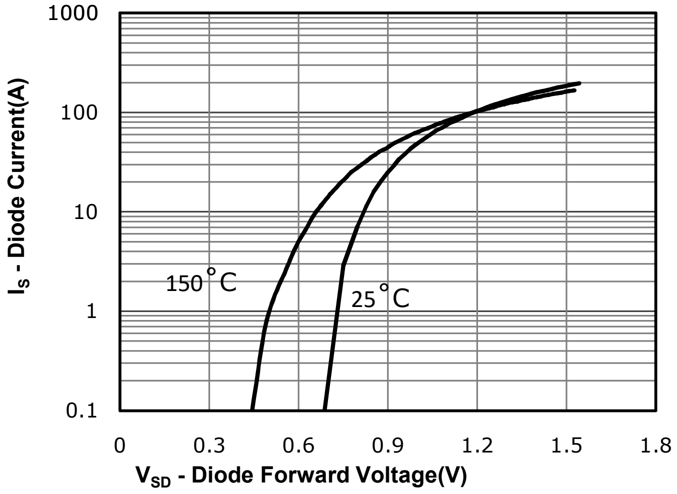


Fig 10: Gate Charge Characteristics

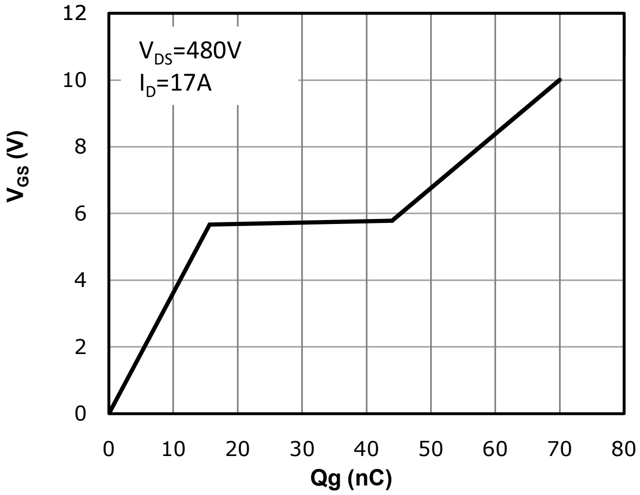


Fig 11: Capacitance Characteristics

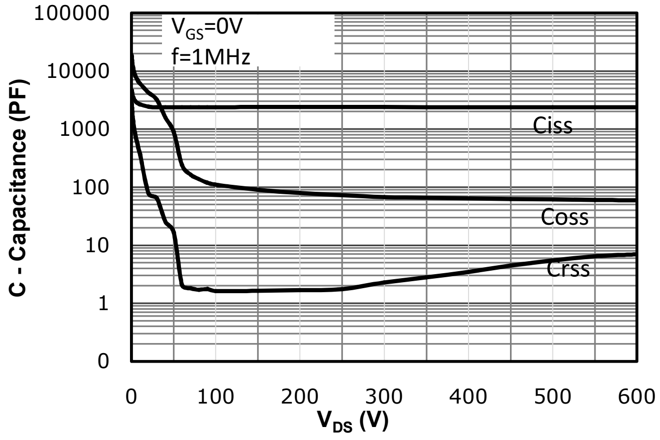


Fig 12: Safe Operating Area

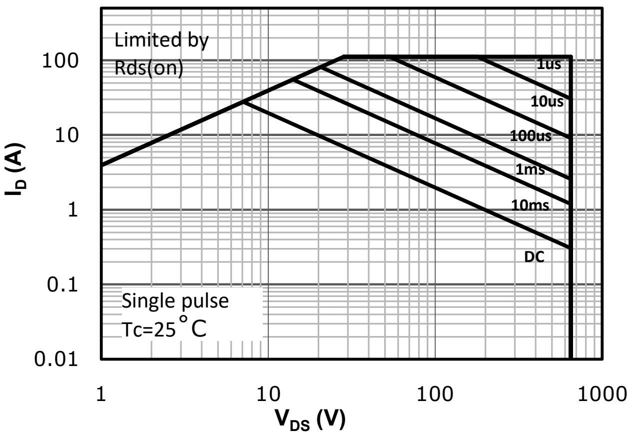
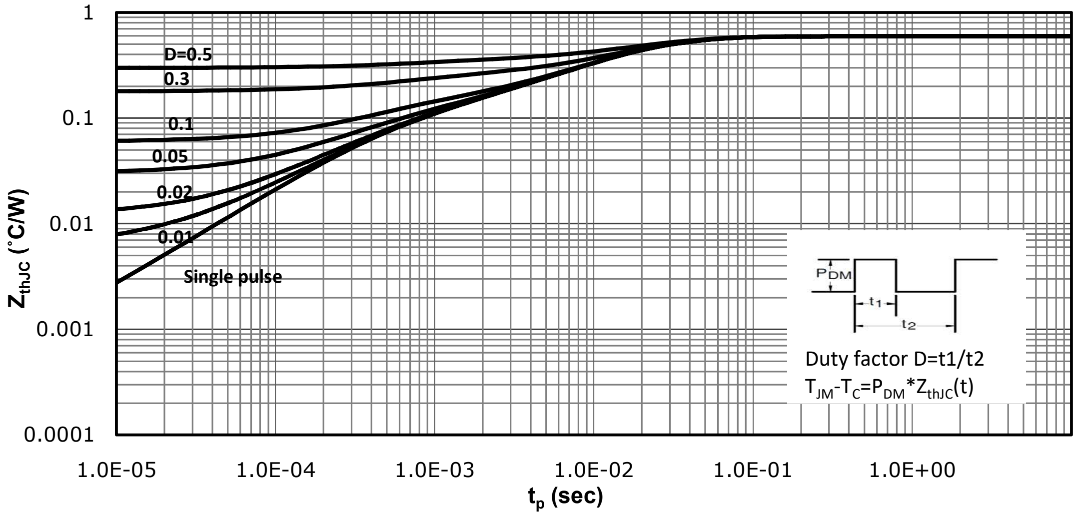
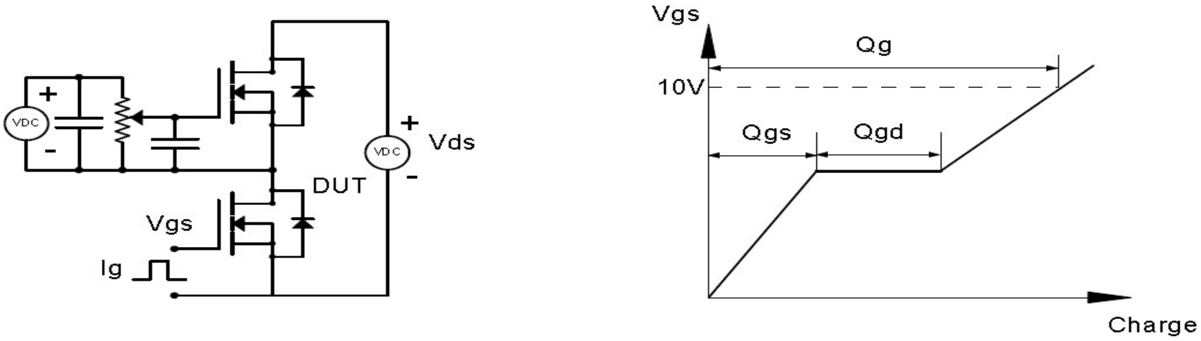


Fig 13: Max. Transient Thermal Impedance

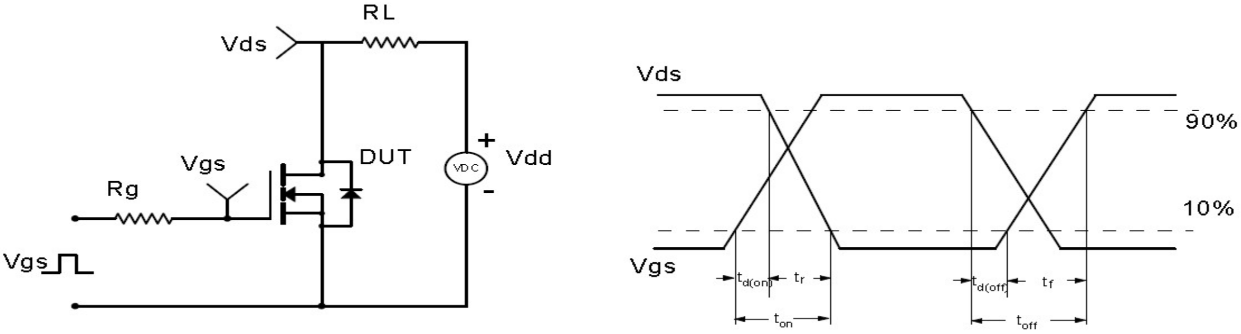


Test Circuit & Waveform

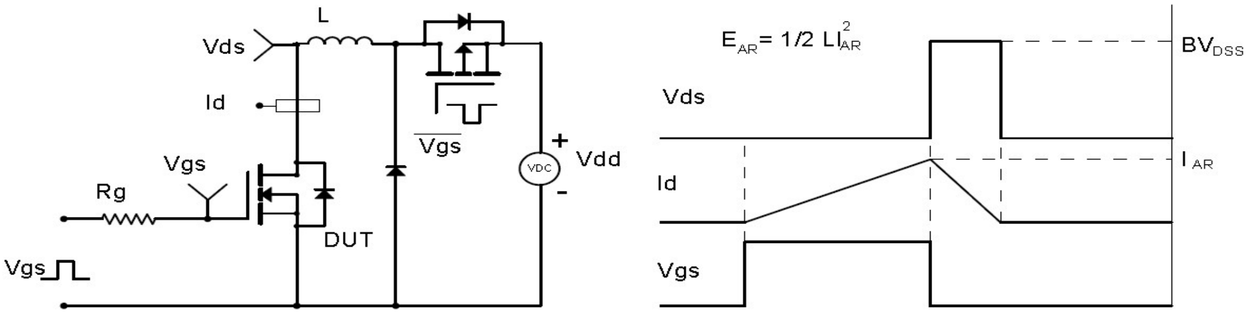
Gate Charge Test Circuit & Waveform



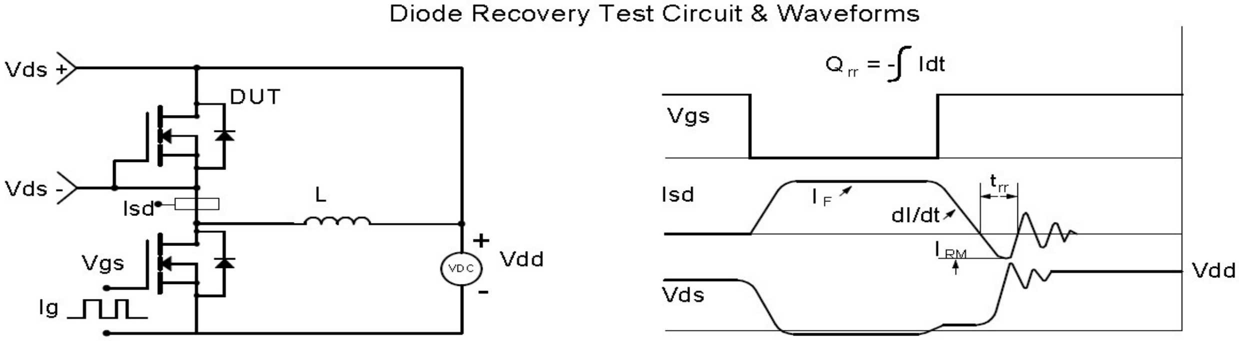
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



Marking

NOTE:
NXBBAAAA
N —Wire bonding code
X —Assembly location code
BB —Fab code
AAAA —Lot code

Revision History

Revison	Date	Major changes
1.0	2023/5/15	First version

Disclaimer

Unless otherwise specified in the datasheet, the product is designed and qulified as a standard commercial product and is not intended for use in applications that require extraordinary levels of quality and reliability, such as automotive, aviation/aerospace and life-support devices or systems.

Any and all semicondutor products have certain probability to fail or malfunction, which may result in personal injury, death or property damage. Customer are solely responsible for providing adequate safe measures when design their systems.

CRM(CQ) reserves the right to improve product design, function and reliability without notice.